

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	$2\Omega@10V$	220mA
	$2.5\Omega@4.5V$	



合肥矽普半导体

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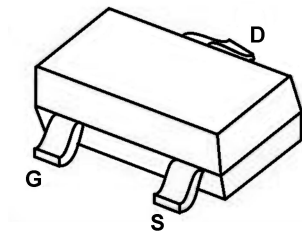
Feature

- High power and current handling capability
- Surface mount package
- ESD protected 2KV

Application

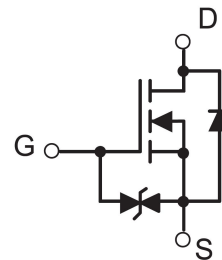
- Battery Switch
- DC/DC Converter

Package

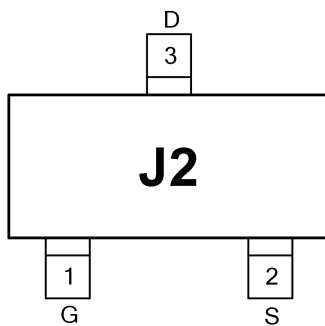


SOT-23

Circuit diagram



Marking



J2 :Device Code

Order Information

Device	Package	Unit/Tape
BSS139	SOT-23	3000

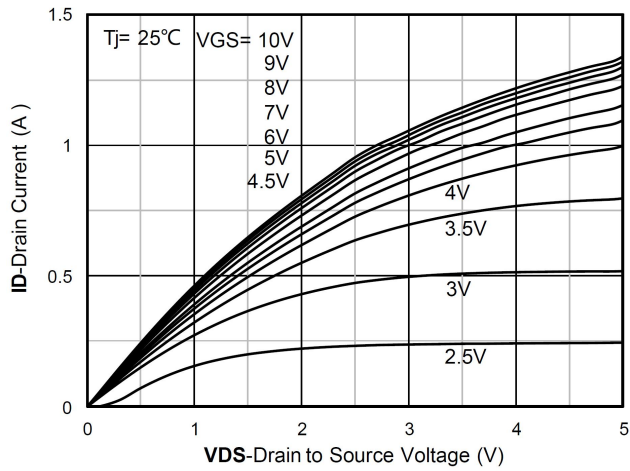
Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	220	mA
Pulse Drain Current Tested	I_{DM}	880	mA
Power Dissipation	P_D	350	mW
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	357	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

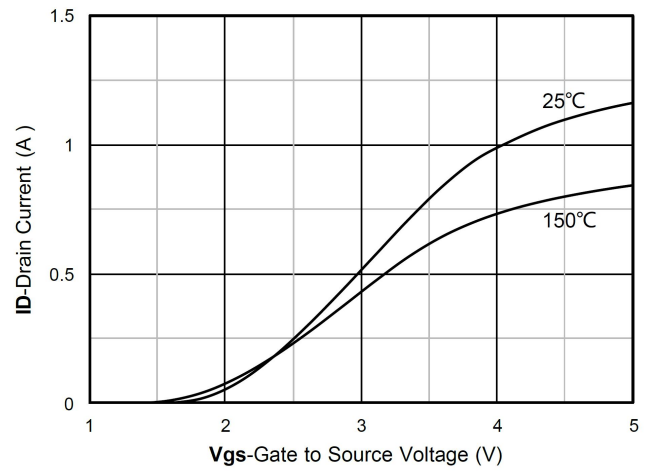
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250μA	60	-	-	V
Drain-Source Leakage Current	I _{DSS}	VDS=48V , VGS=0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	VGS=±20V , VDS=0V	-	-	±10	uA
Gate Threshold Voltage	V _{GS(th)}	VDS=VGS , ID=250μA	0.7	1	1.45	V
Static Drain-Source On-Resistance	R _{DS(ON)}	VGS =10V, ID =500mA	-	2	5	Ω
		VGS =4.5V, ID =200mA	-	2.5	8	
Dynamic characteristics						
Input Capacitance	C _{iss}	VDS=25V , VGS=0V , f=1MHz	-	12	-	pF
Output Capacitance	C _{oss}		-	6	-	
Reverse Transfer Capacitance	C _{rss}		-	2.5	-	
Total Gate Charge	Q _g	VDS=10V , VGS=15V , ID=1A	-	1.34	-	nC
Gate-Source Charge	Q _{gs}		-	0.29	-	
Gate-Drain Charge	Q _{gd}		-	0.2	-	
Switching Characteristics						
Turn-On Delay Time	t _{d(on)}	VDD=15V VGS=10V , RG=2.3Ω , ID=1A	-	5	-	nS
Turn-On Rise Time	t _r		-	18	-	
Turn-Off Delay Time	t _{d(off)}		-	8	-	
Turn-Off Fall Time	t _f		-	14	-	
Source-Drain Diode characteristics						
Diode Forward Voltage	V _{SD}	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V

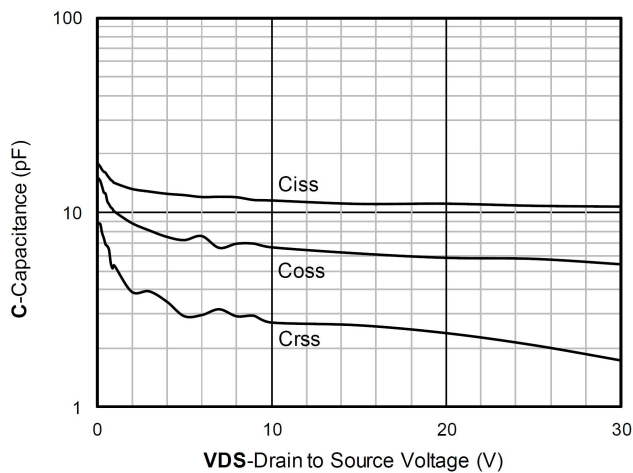
Typical Characteristics



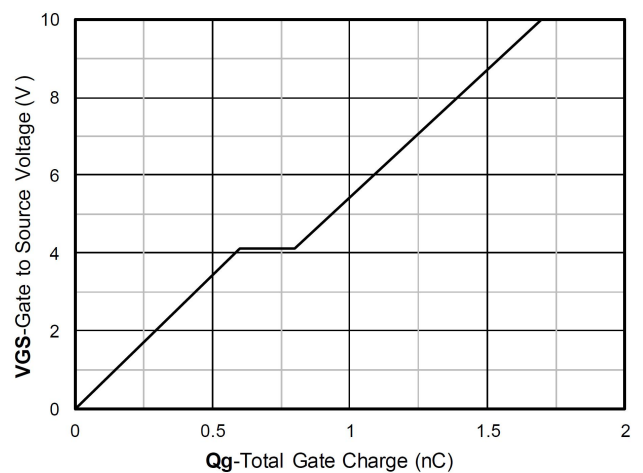
Output Characteristics



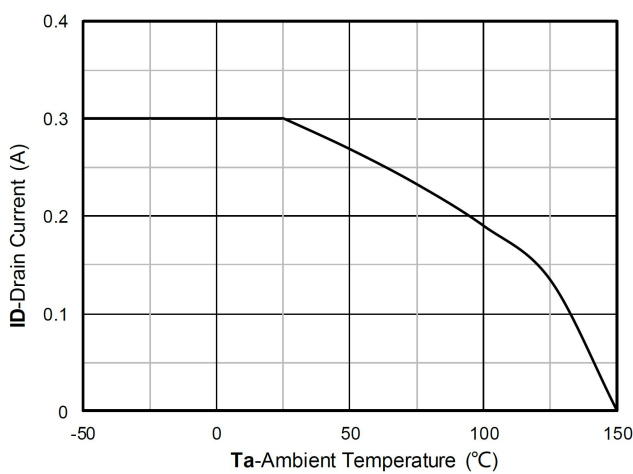
Transfer Characteristics



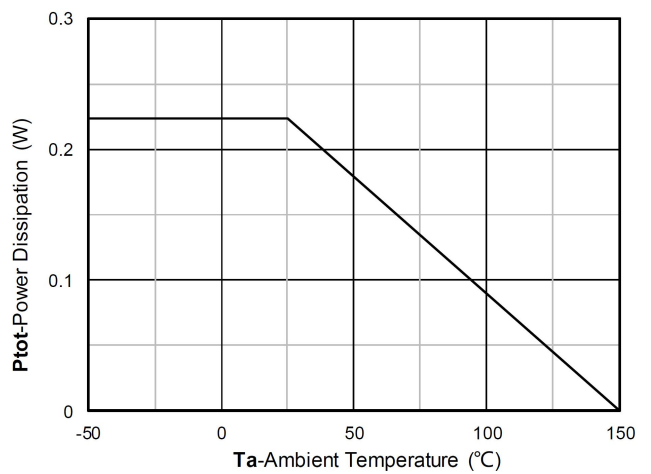
Capacitance Characteristics



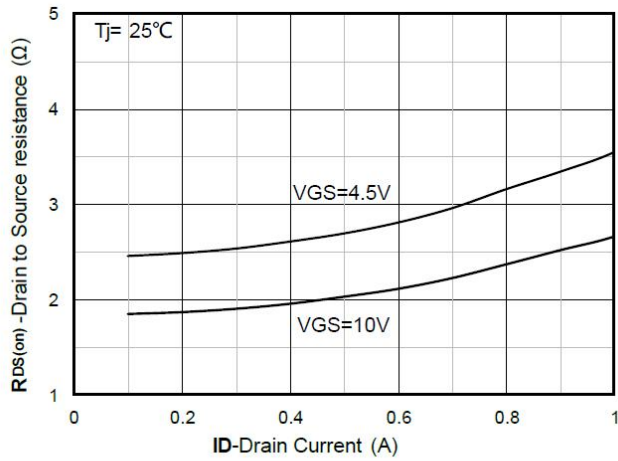
Gate Charge



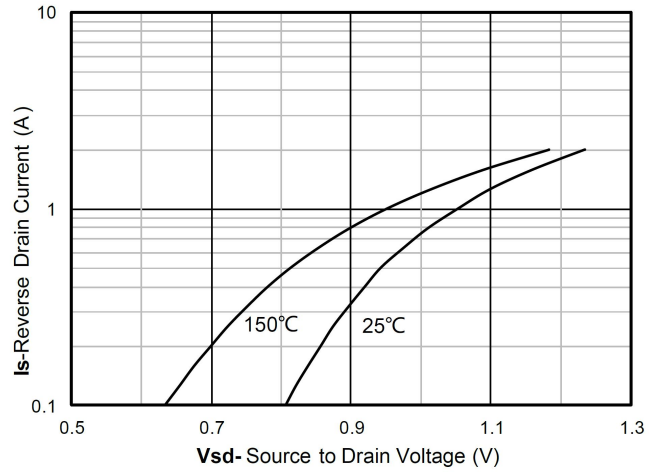
Current dissipation



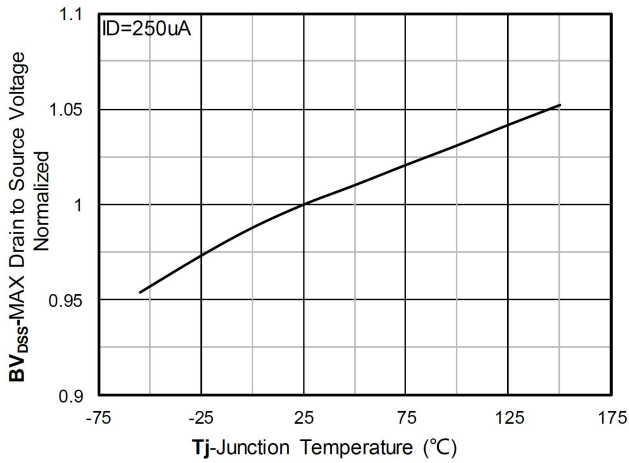
Power dissipation



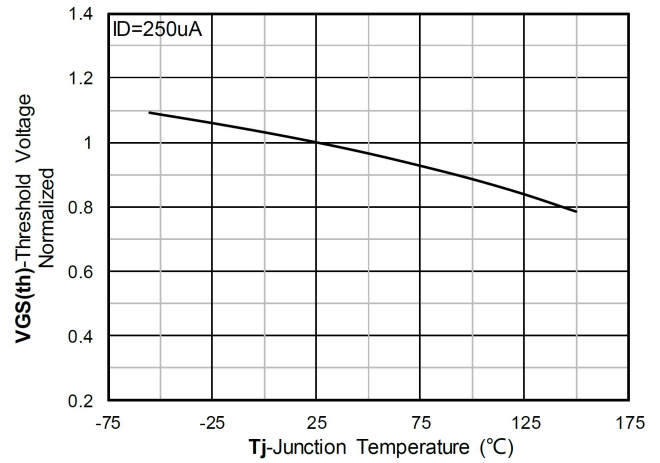
RDS(on) VS Drain Current



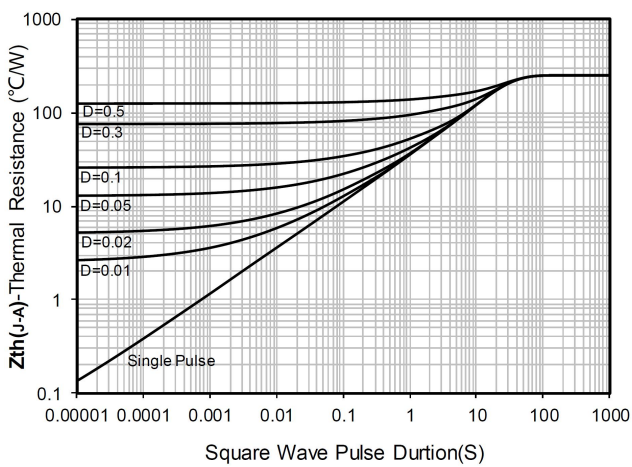
Forward characteristics of reverse diode



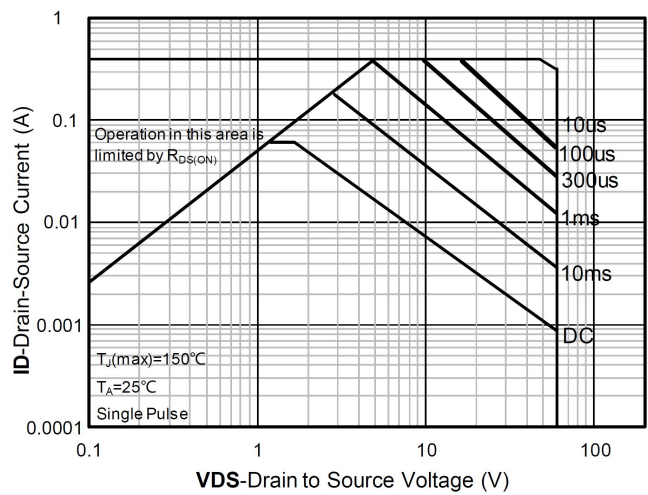
Normalized breakdown voltage



Normalized Threshold voltage

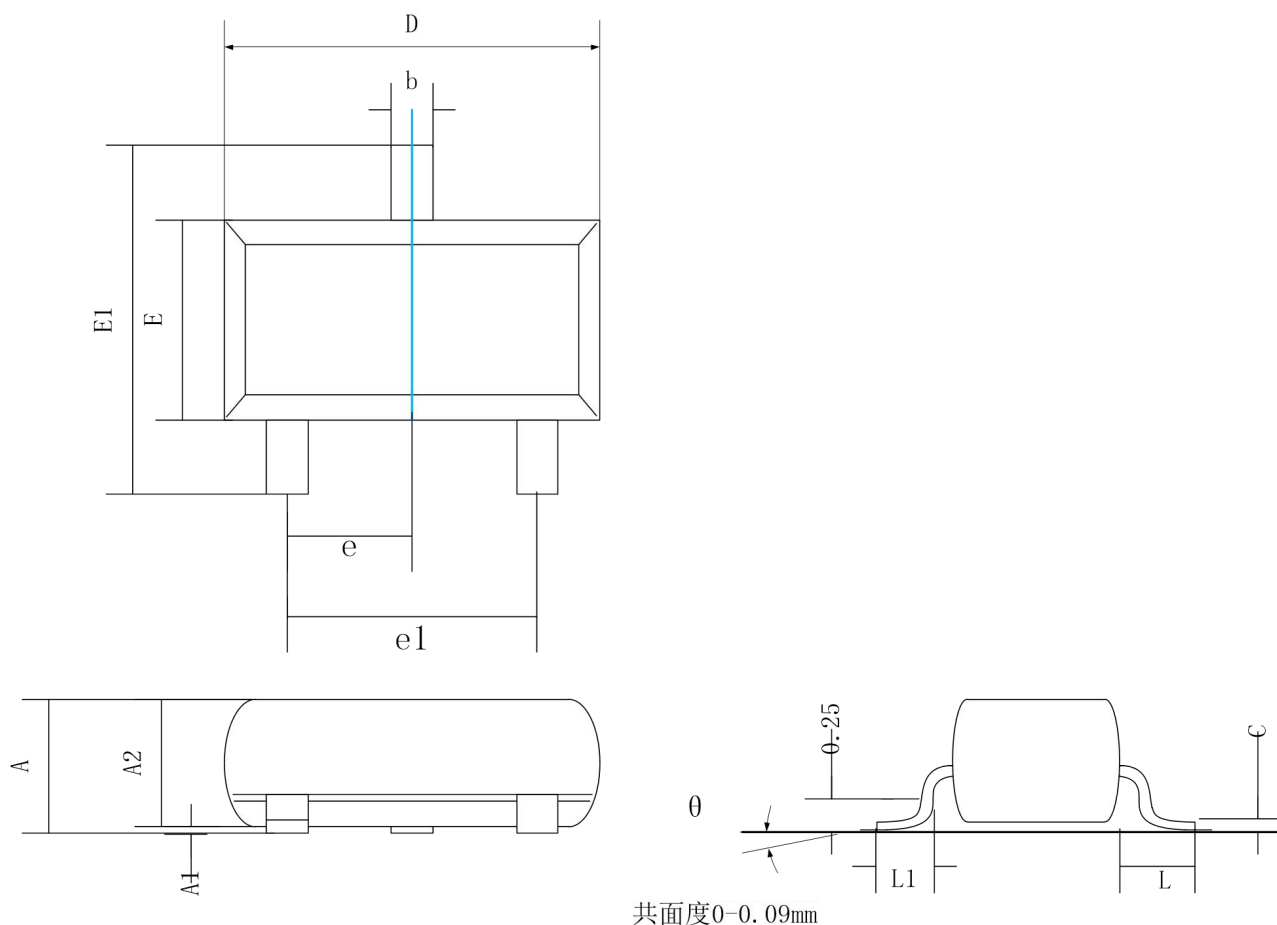


Maximum Transient Thermal Impedance



Safe Operation Area

SOT-23 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50
θ	0°	8°